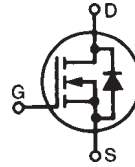


**Polar™  
Power MOSFET**
**IXTQ69N30PM**

$$V_{DSS} = 300V$$

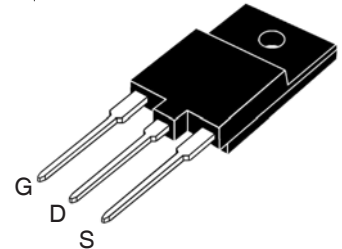
$$I_{D25} = 25A$$

$$R_{DS(on)} \leq 49m\Omega$$



N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode

**OVERMOLDED  
(IXTQ...M) OUTLINE**



G = Gate      D = Drain  
S = Source

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	300	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1 M\Omega$	300	V
$V_{GSS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ C$	25	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	200	A
$I_A$	$T_C = 25^\circ C$	69	A
$E_{AS}$	$T_C = 25^\circ C$	1.5	J
$dv/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J = 150^\circ C$	15	V/ns
$P_D$	$T_C = 25^\circ C$	90	W
$T_J$		- 55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		- 55 ... +150	$^\circ C$
$T_L$	1.6 mm (0.062 in.) from Case for 10 s	300	$^\circ C$
$T_{SOLD}$	Plastic Body for 10 s	260	$^\circ C$
$M_d$	Mounting Torque	1.13/10	Nm/lb.in.
<b>Weight</b>		2.5	g

**Features**

- Plastic Overmolded Tab for Electrical Isolation
- Avalanche Rated
- Fast Intrinsic Diode
- Low Package Inductance

**Advantages**

- High Power Density
- Easy to Mount
- Space Savings

**Applications**

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

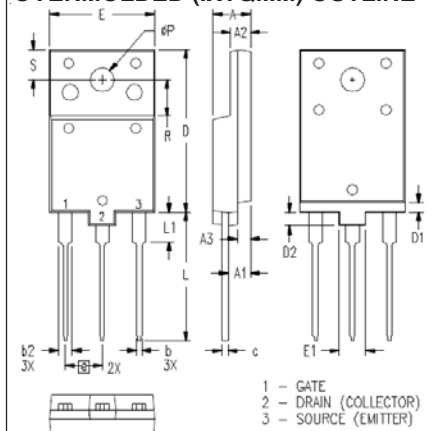
Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 250\mu A$	300		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	2.5		5.0 V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 100$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ C$			5 $\mu A$ 100 $\mu A$
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 34.5A$ , Note 1			49 m $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{V}$ , $I_D = 34.5\text{A}$ , Note 1	27	45	S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		4960	pF
$C_{oss}$			760	pF
$C_{rss}$			190	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 34.5\text{A}$ $R_G = 4\Omega$ (External)		25	ns
$t_r$			25	ns
$t_{d(off)}$			75	ns
$t_f$			27	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 34.5\text{A}$		156	nC
$Q_{gs}$			32	nC
$Q_{gd}$			79	nC
$R_{thJC}$				1.38 $^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			69 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			270 A
$V_{SD}$	$I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = 25\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$ , $V_{GS} = 0\text{V}$		250	ns
$Q_{RM}$			3.0	$\mu\text{C}$

### OVERMOLDED (IQTQ...M) OUTLINE



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.213	.228	5.40	5.80
A1	.122	.138	3.10	3.50
A2	.114	.130	2.90	3.30
A3	.075	.091	1.90	2.30
b	.026	.037	0.65	0.95
b2	.075	.091	1.90	2.30
c	.031	.043	0.80	1.10
D	.957	.972	24.30	24.70
D1	.051	.067	1.30	1.70
D2	.071	.087	1.80	2.20
E	.606	.622	15.40	15.80
E1	.154	.169	3.90	4.30
e	.215 BSC		5.45 BSC	
L	.748	.768	19.00	19.50
L1	.169	.185	4.30	4.70
$\phi P$	.134	.150	3.40	3.80
R	.209	.224	5.30	5.70
S	.169	.185	4.30	4.70

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

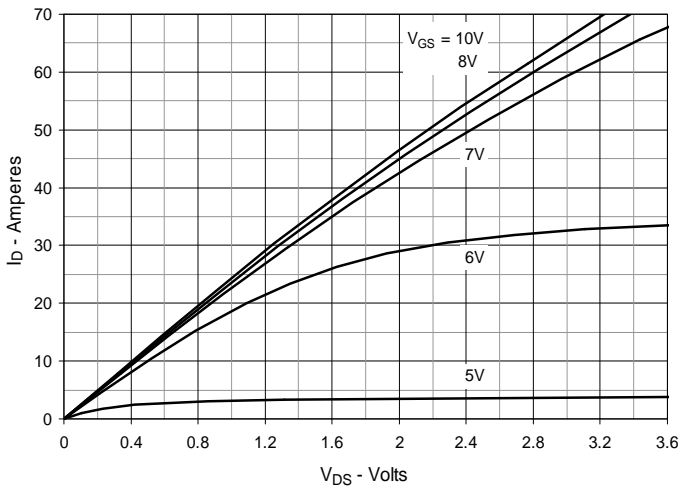
### ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

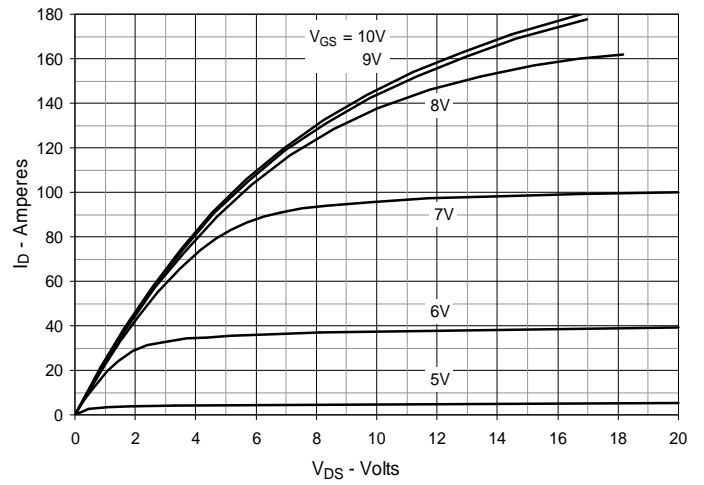
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

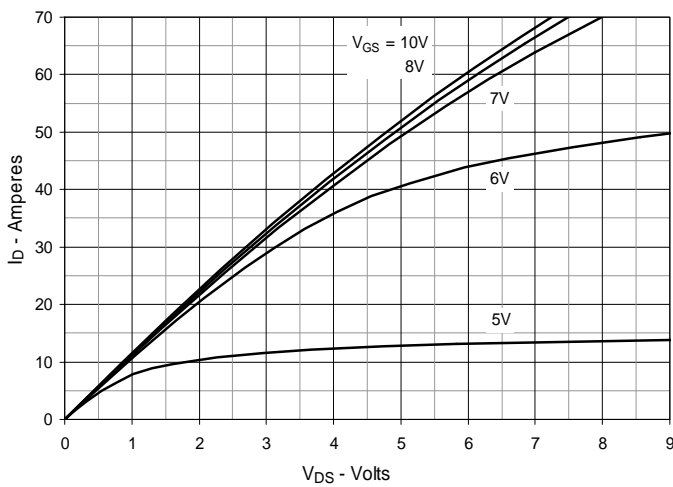
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



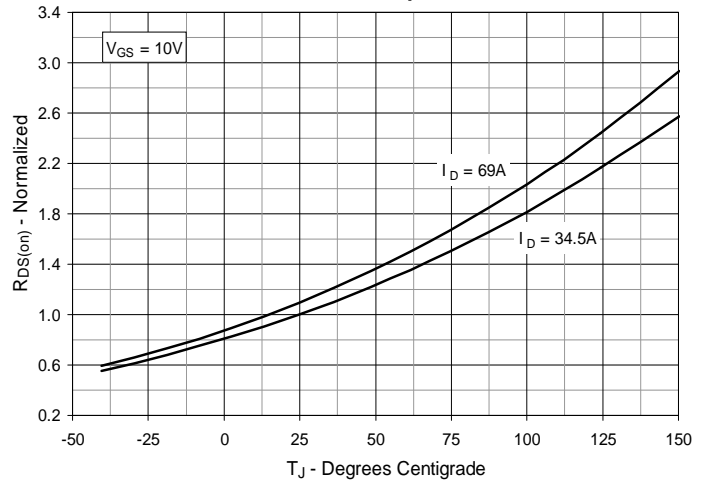
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



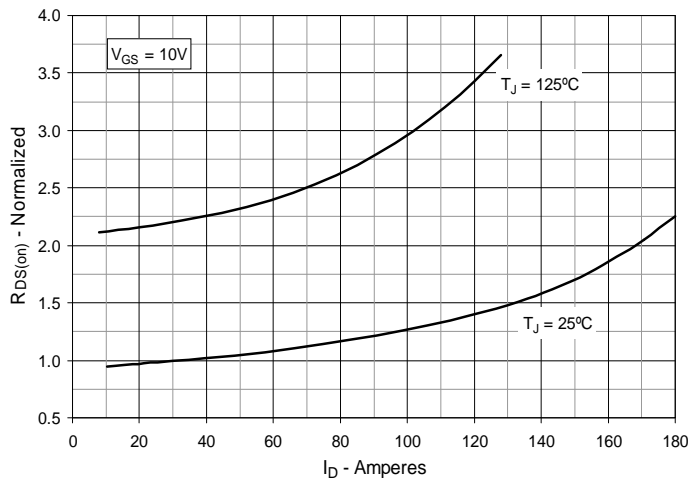
**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$**



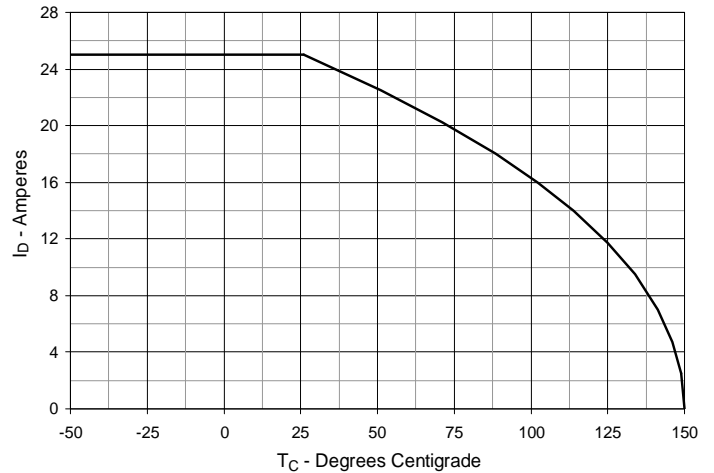
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 34.5\text{A}$  Value vs. Junction Temperature**



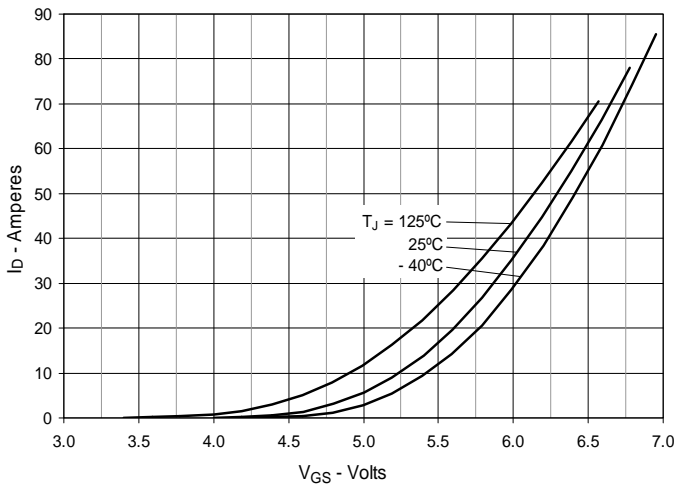
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 34.5\text{A}$  Value vs. Drain Current**



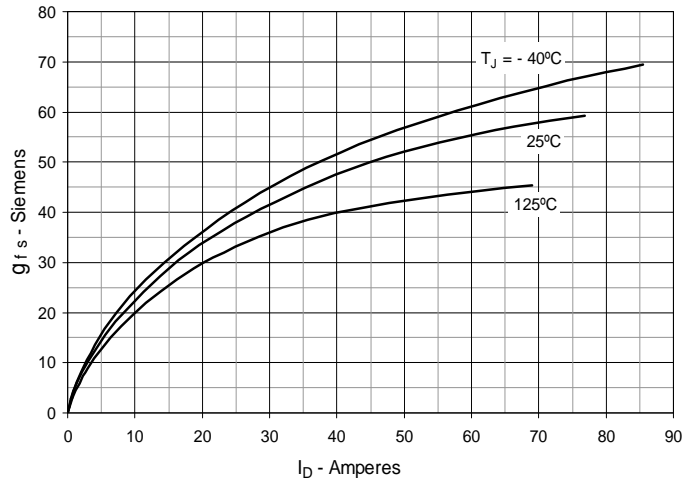
**Fig. 6. Maximum Drain Current vs. Case Temperature**



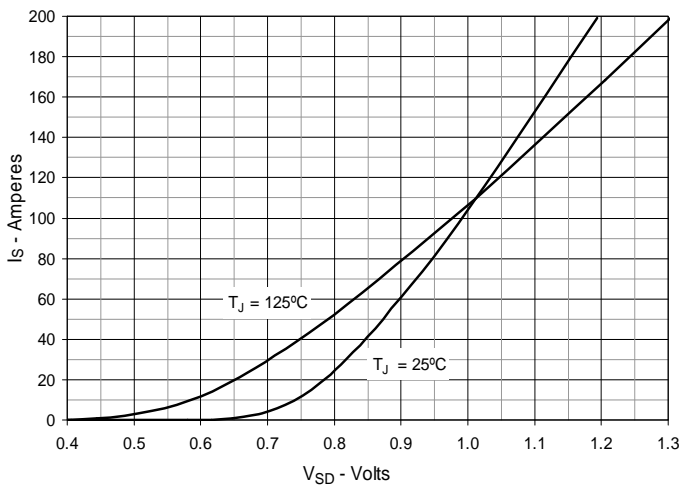
**Fig. 7. Input Admittance**



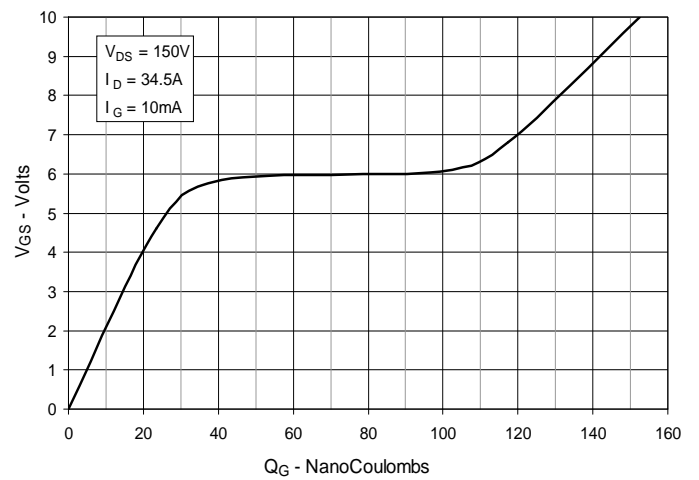
**Fig. 8. Transconductance**



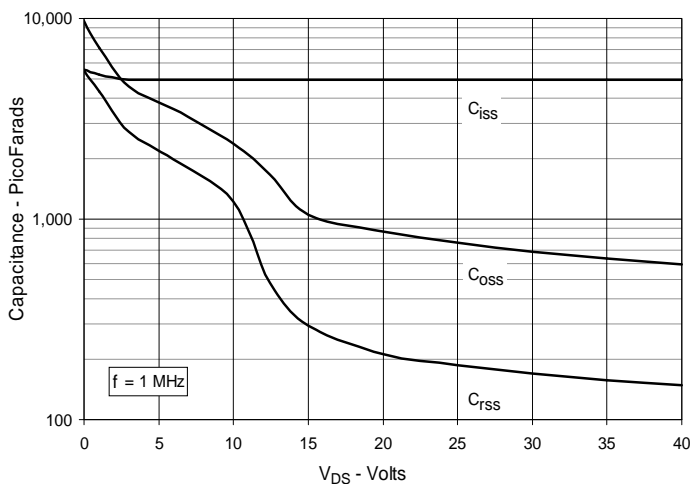
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



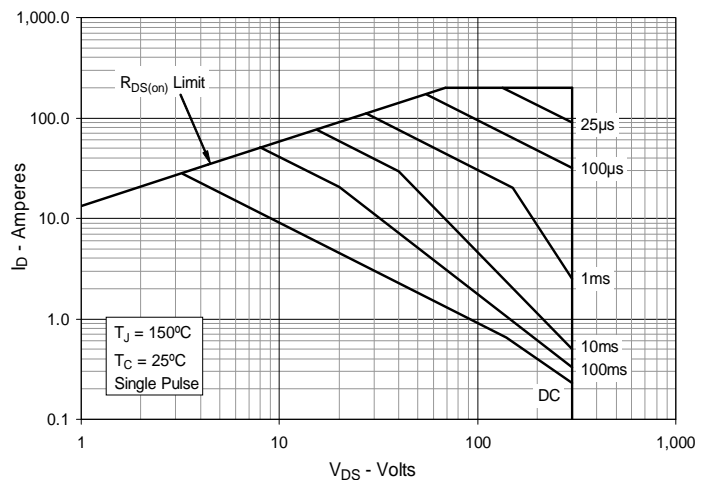
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Forward-Bias Safe Operating Area**



IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

Fig. 13. Maximum Transient Thermal Impedance

